

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING
APPARATUS

ABSTRACT

There is provided a technique that includes: (a) supplying a first gas containing a Group 14 element to a substrate including a recess; (b) supplying a second gas containing a Group 15 or Group 13 element to the substrate; (c) forming a first film containing the Group 14 element in the recess by performing (a) and (b) with the second gas at a first concentration, and stopping film formation before the recess is filled up with the first film; and (d) after (c), performing (b) with the second gas at a second concentration and heat-treating the substrate.

Fig. 4